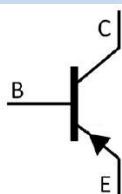


SOT-23 PNP Silicon PNP transistor in a SOT-23 Plastic Package.

2SD2444K
 Low $V_{CE(sat)}$, large current, complementary to 2SD2444K.

General power amplifier applications.

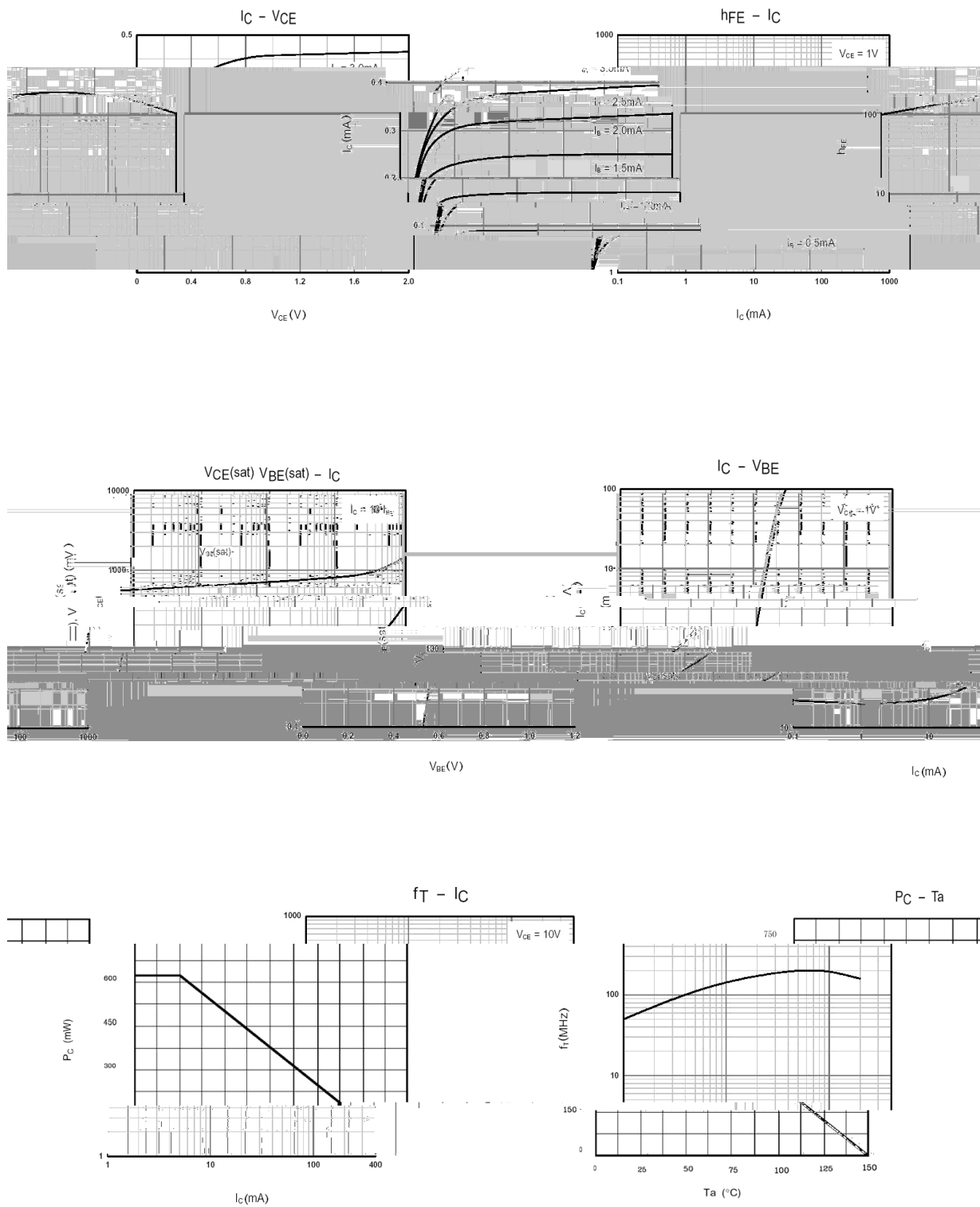


PIN 1 Base PIN 2 Emitter PIN 3 Collector

h_{FE} Classifications Symbol	Q
h_{FE} Range	120 270
Marking	HBKQ

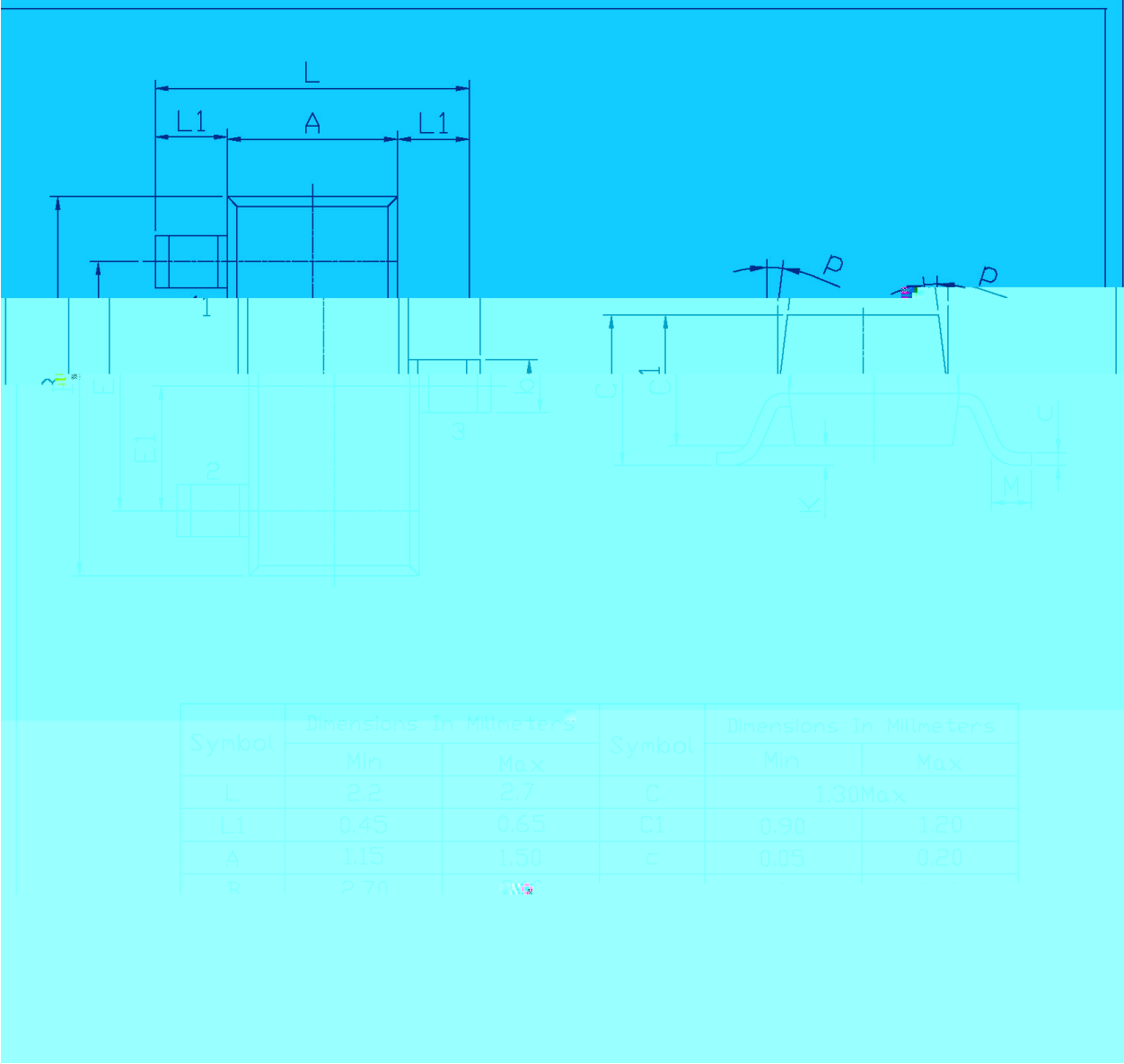
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-15	V
Collector to Emitter Voltage	V_{CEO}	-15	V
Emitter to Base Voltage	V_{EBO}	-6.0	V
Collector Current	I_C	-1.0	A
Collector Current	I_{CM}	-3.0	A
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -50\text{ A}$ $I_B = 0$	-15			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -1.0\text{mA}$ $I_E = 0$	-15			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E = -50\text{ A}$ $I_C = 0$	-6.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -12\text{V}$ $I_E = 0$			-0.5	A
Emitter Cut-Off Current	I_{EBO}	$V_{CE} = -5.0\text{V}$ $I_C = 0$			-0.5	A
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -2.0\text{V}$ $I_C = -50\text{mA}$	120		270	
	$h_{FE(2)}$	$V_{CE} = -2.0\text{V}$ I				



SOT-23

单位: mm





H

BK:

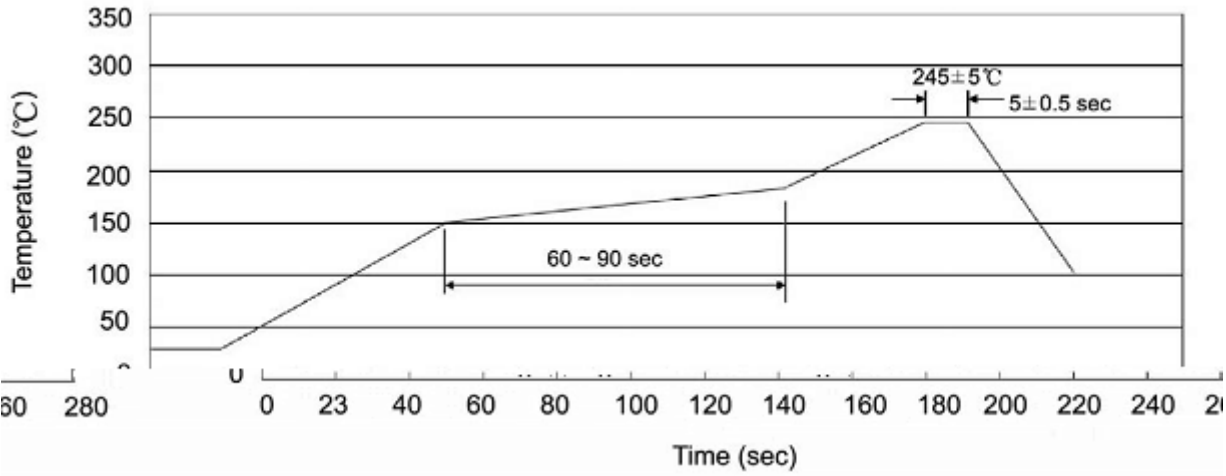
Q: h_{FE}

Note:

H Company Code

BK Product Type Code

Q: h_{FE} Classifications Symbol Code



Note:

- | | | | | | |
|---|-------|-----|----|-----------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 245±5 | | | 5±0.5sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ REEL

Package Type 封装 式	Units 包装 量					Dimension 包装尺寸 (unit: mm ³)		
	卷盘	卷盘 盒	盒	盒			盒	